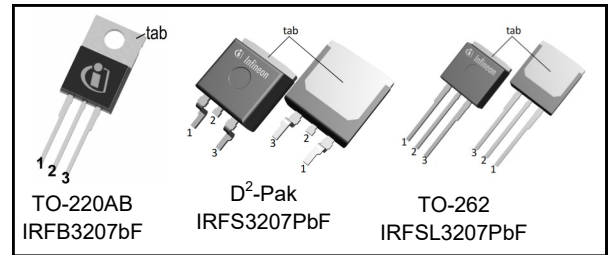
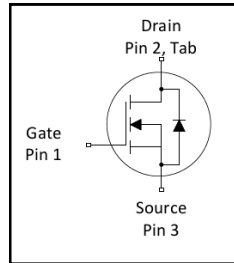


|                          |                                                |
|--------------------------|------------------------------------------------|
| $V_{(BR)DSS}$            | <b>75V</b>                                     |
| $R_{DS(on)}$ <b>typ.</b> | <b>3.6m<math>\Omega</math></b>                 |
|                          | <b>max.</b> <b>4.5m<math>\Omega</math></b>     |
| $I_D$                    | <b>170A<math>\text{\textcircled{D}}</math></b> |



## Applications

- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits

| <b>G</b> | <b>D</b> | <b>S</b> |
|----------|----------|----------|
| Gate     | Drain    | Source   |

## Benefits

- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dv/dt and di/dt Capability
- Lead-Free

| Base part number | Package Type | Standard Pack |          | Orderable Part Number |
|------------------|--------------|---------------|----------|-----------------------|
|                  |              | Form          | Quantity |                       |
| IRFB3207PbF      | TO-220       | Tube          | 50       | IRFB3207PbF           |
| IRFS3207PbF      | D²-Pak       | Tape and Reel | 800      | IRFS3207PbF           |
| IRFSL3207PbF     | TO-262       | Tube          | 50       | IRFSL3207PbF          |

## Absolute Maximum Ratings

| Symbol                            | Parameter                                               | Max.                         | Units               |
|-----------------------------------|---------------------------------------------------------|------------------------------|---------------------|
| $I_D$ @ $T_C = 25^\circ\text{C}$  | Continuous Drain Current, $V_{GS}$ @ 10V                | 170 $\text{\textcircled{D}}$ | A                   |
| $I_D$ @ $T_C = 100^\circ\text{C}$ | Continuous Drain Current, $V_{GS}$ @ 10V                | 120 $\text{\textcircled{D}}$ |                     |
| $I_{DM}$                          | Pulsed Drain Current $\text{\textcircled{2}}$           | 720                          |                     |
| $P_D$ @ $T_C = 25^\circ\text{C}$  | Maximum Power Dissipation                               | 320                          | W                   |
|                                   | Linear Derating Factor                                  | 2.0                          | W/ $^\circ\text{C}$ |
| $V_{GS}$                          | Gate-to-Source Voltage                                  | $\pm 20$                     | V                   |
| dv/dt                             | Peak Diode Recovery $\text{\textcircled{4}}$            | 5.8                          | V/ns                |
| $T_J$                             | Operating Junction and                                  | -55 to + 175                 | $^\circ\text{C}$    |
| $T_{STG}$                         | Storage Temperature Range                               |                              |                     |
|                                   | Soldering Temperature, for 10 seconds (1.6mm from case) | 300                          |                     |
|                                   | Mounting torque, 6-32 or M3 screw                       | 10 lbf•in (1.1N•m)           |                     |

## Avalanche Characteristics

|          |                                                                            |                         |    |
|----------|----------------------------------------------------------------------------|-------------------------|----|
| $E_{AS}$ | Single Pulse Avalanche Energy (Thermally Limited) $\text{\textcircled{3}}$ | 910                     | mJ |
| $I_{AR}$ | Avalanche Current $\text{\textcircled{2}}$                                 | See Fig.14,15, 22a, 22b | A  |
| $E_{AR}$ | Repetitive Avalanche Energy $\text{\textcircled{5}}$                       |                         | mJ |

## Thermal Resistance

| Symbol          | Parameter                                                                                 | Typ. | Max. | Units              |
|-----------------|-------------------------------------------------------------------------------------------|------|------|--------------------|
| $R_{\theta JC}$ | Junction-to-Case $\text{\textcircled{9}}$                                                 | —    | 0.50 | $^\circ\text{C/W}$ |
| $R_{\theta CS}$ | Case-to-Sink, Flat, Greased Surface, TO-220                                               | 0.50 | —    |                    |
| $R_{\theta JA}$ | Junction-to-Ambient, TO-220 $\text{\textcircled{9}}$                                      | —    | 62   |                    |
| $R_{\theta JA}$ | Junction-to-Ambient (PCB Mount), D² Pak $\text{\textcircled{8}}$ $\text{\textcircled{9}}$ | —    | 40   |                    |

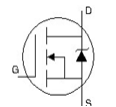
Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

|                                 | Parameter                            | Min. | Typ.  | Max. | Units               | Conditions                                           |
|---------------------------------|--------------------------------------|------|-------|------|---------------------|------------------------------------------------------|
| $V_{(BR)DSS}$                   | Drain-to-Source Breakdown Voltage    | 75   | —     | —    | V                   | $V_{GS} = 0V, I_D = 250\mu A$                        |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient  | —    | 0.069 | —    | V/ $^\circ\text{C}$ | Reference to $25^\circ\text{C}$ , $I_D = 1mA$ ②      |
| $R_{DS(on)}$                    | Static Drain-to-Source On-Resistance | —    | 3.6   | 4.5  | m $\Omega$          | $V_{GS} = 10V, I_D = 75A$ ⑤                          |
| $V_{GS(th)}$                    | Gate Threshold Voltage               | 2.0  | —     | 4.0  | V                   | $V_{DS} = V_{GS}, I_D = 250\mu A$                    |
| $I_{DSS}$                       | Drain-to-Source Leakage Current      | —    | —     | 20   | $\mu A$             | $V_{DS} = 75V, V_{GS} = 0V$                          |
|                                 |                                      | —    | —     | 250  |                     | $V_{DS} = 75V, V_{GS} = 0V, T_J = 125^\circ\text{C}$ |
| $I_{GSS}$                       | Gate-to-Source Forward Leakage       | —    | —     | 200  | nA                  | $V_{GS} = 20V$                                       |
|                                 | Gate-to-Source Reverse Leakage       | —    | —     | -200 |                     | $V_{GS} = -20V$                                      |
| $R_G$                           | Gate Resistance                      | —    | 1.2   | —    | $\Omega$            | $f = 1.0MHz$ , open drain                            |

Dynamic Electrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

|                           |                                               |     |      |     |    |                                       |
|---------------------------|-----------------------------------------------|-----|------|-----|----|---------------------------------------|
| gfs                       | Forward Trans conductance                     | 150 | —    | —   | S  | $V_{DS} = 50V, I_D = 75A$             |
| $Q_g$                     | Total Gate Charge                             | —   | 180  | 260 | nC | $I_D = 75A$                           |
| $Q_{gs}$                  | Gate-to-Source Charge                         | —   | 48   | —   |    | $V_{DS} = 60V$                        |
| $Q_{gd}$                  | Gate-to-Drain Charge                          | —   | 68   | —   |    | $V_{GS} = 10V$ ⑤                      |
| $t_{d(on)}$               | Turn-On Delay Time                            | —   | 29   | —   | ns | $V_{DD} = 48V$                        |
| $t_r$                     | Rise Time                                     | —   | 120  | —   |    | $I_D = 75A$                           |
| $t_{d(off)}$              | Turn-Off Delay Time                           | —   | 68   | —   |    | $R_G = 2.6\Omega$                     |
| $t_f$                     | Fall Time                                     | —   | 74   | —   |    | $V_{GS} = 10V$ ⑤                      |
| $C_{iss}$                 | Input Capacitance                             | —   | 7600 | —   | pF | $V_{GS} = 0V$                         |
| $C_{oss}$                 | Output Capacitance                            | —   | 710  | —   |    | $V_{DS} = 50V$                        |
| $C_{rss}$                 | Reverse Transfer Capacitance                  | —   | 390  | —   |    | $f = 1.0MHz$ , See Fig. 5             |
| $C_{oss\text{ eff.}(ER)}$ | Effective Output Capacitance (Energy Related) | —   | 920  | —   |    | $V_{GS} = 0V, V_{DS} = 0V$ to $60V$ ⑦ |
| $C_{oss\text{ eff.}(TR)}$ | Effective Output Capacitance (Time Related)   | —   | 1010 | —   |    | $V_{GS} = 0V, V_{DS} = 0V$ to $60V$ ⑧ |

## Diode Characteristics

|           | Parameter                              | Min. | Typ. | Max.  | Units | Conditions                                                                                                                                           |
|-----------|----------------------------------------|------|------|-------|-------|------------------------------------------------------------------------------------------------------------------------------------------------------|
| $I_S$     | Continuous Source Current (Body Diode) | —    | —    | 170 ① | A     | MOSFET symbol showing the integral reverse p-n junction diode.  |
| $I_{SM}$  | Pulsed Source Current (Body Diode) ②   | —    | —    | 720   |       |                                                                                                                                                      |
| $V_{SD}$  | Diode Forward Voltage                  | —    | —    | 1.3   | V     | $T_J = 25^\circ\text{C}, I_S = 75A, V_{GS} = 0V$ ⑤                                                                                                   |
| $t_{rr}$  | Reverse Recovery Time                  | —    | 42   | 63    | ns    | $T_J = 25^\circ\text{C}$ $V_{DD} = 64V$                                                                                                              |
|           |                                        | —    | 49   | 74    |       | $T_J = 125^\circ\text{C}$ $I_F = 75A$ ,                                                                                                              |
| $Q_{rr}$  | Reverse Recovery Charge                | —    | 65   | 98    | nC    | $T_J = 25^\circ\text{C}$ $di/dt = 100A/\mu s$ ⑤                                                                                                      |
|           |                                        | —    | 92   | 140   |       | $T_J = 125^\circ\text{C}$                                                                                                                            |
| $I_{RRM}$ | Reverse Recovery Current               | —    | 2.6  | —     | A     | $T_J = 25^\circ\text{C}$                                                                                                                             |

## Notes:

- ① Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ Limited by  $T_{Jmax}$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.33mH$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 75A$ ,  $V_{GS} = 10V$ . Part not recommended for use above this value.
- ④  $I_{SD} \leq 75A$ ,  $di/dt \leq 500A/\mu s$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 175^\circ\text{C}$ .
- ⑤ Pulse width  $\leq 400\mu s$ ; duty cycle  $\leq 2\%$ .
- ⑥  $C_{oss\text{ eff.}(TR)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑦  $C_{oss\text{ eff.}(ER)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑧ when mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note# [AN-994](#).
- ⑨  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$ .

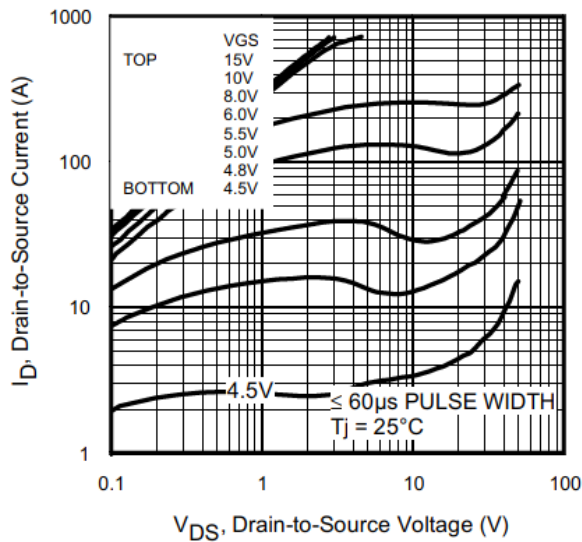


Fig. 1 Typical Output Characteristics

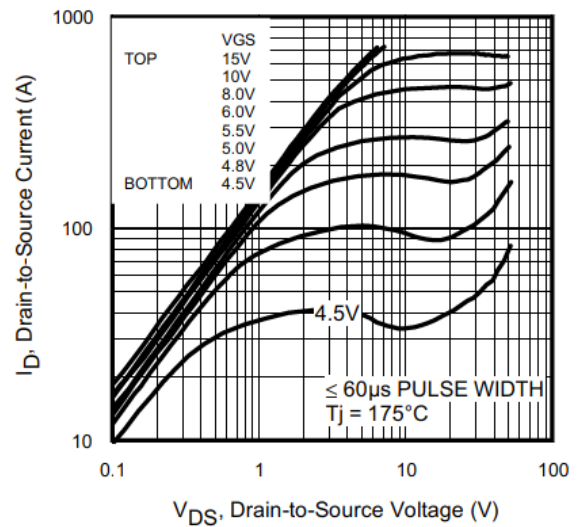


Fig. 2 Typical Output Characteristics

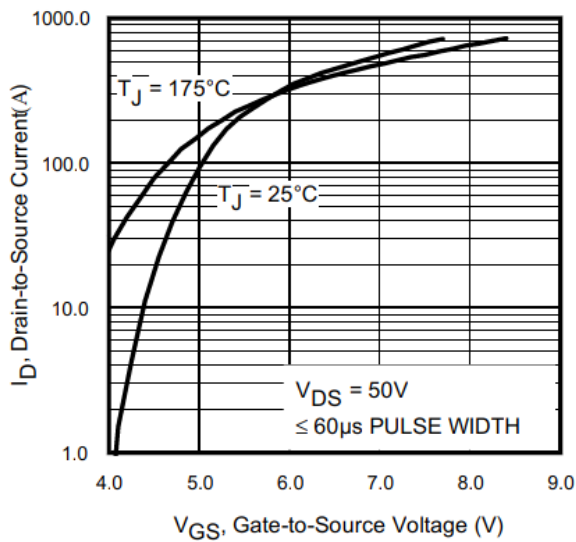


Fig. 3 Typical Transfer Characteristics

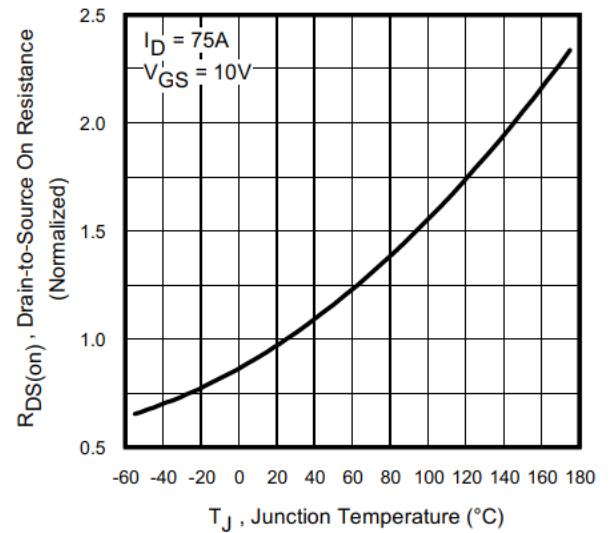


Fig. 4 Normalized On-Resistance vs. Temperature

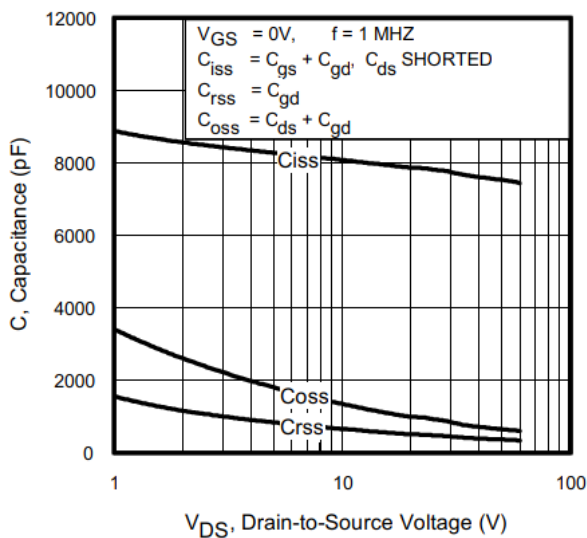


Fig. 5. Typical Capacitance vs. Drain-to-Source Voltage

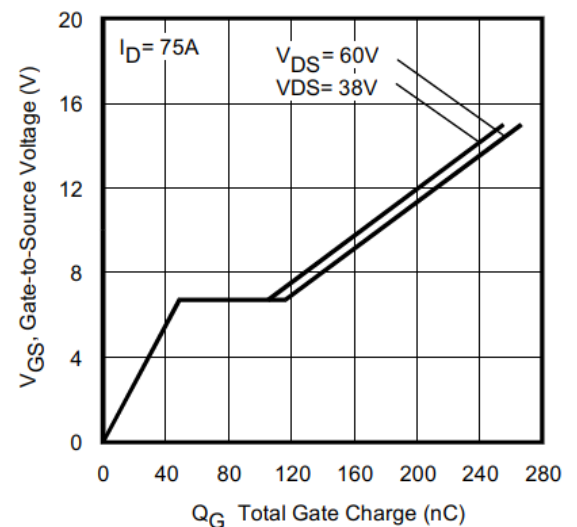


Fig. 6. Typical Gate Charge vs. Gate-to-Source Voltage

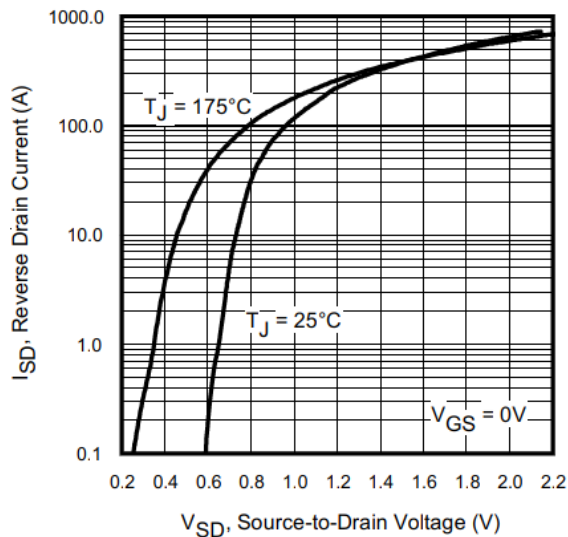


**Fig. 7** Typical Source-to-Drain Diode Forward Voltage

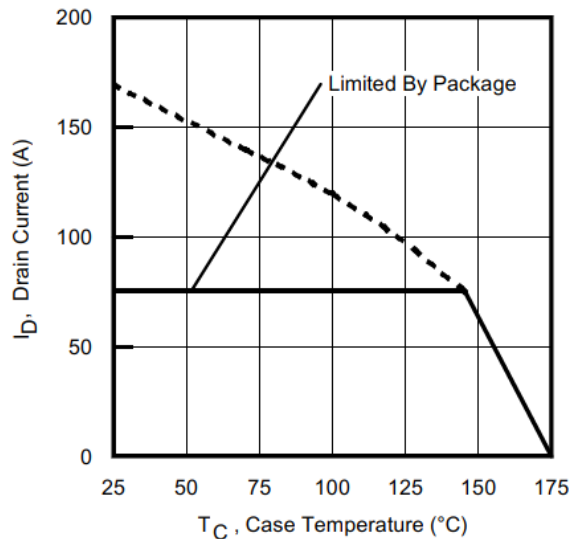


**Fig 9.** Maximum Drain Current vs. Case Temperature

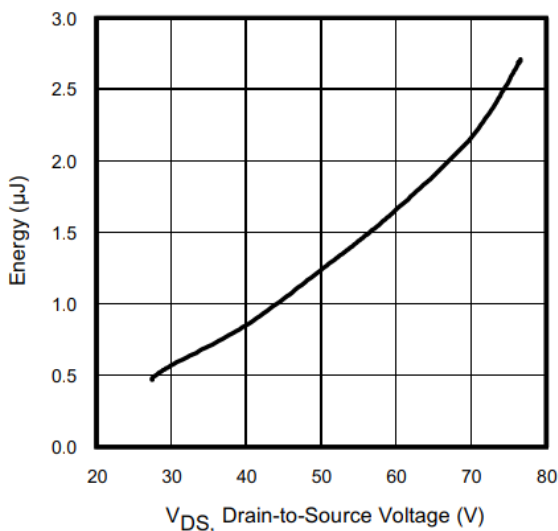


**Fig 11.** Typical Coss Stored Energy

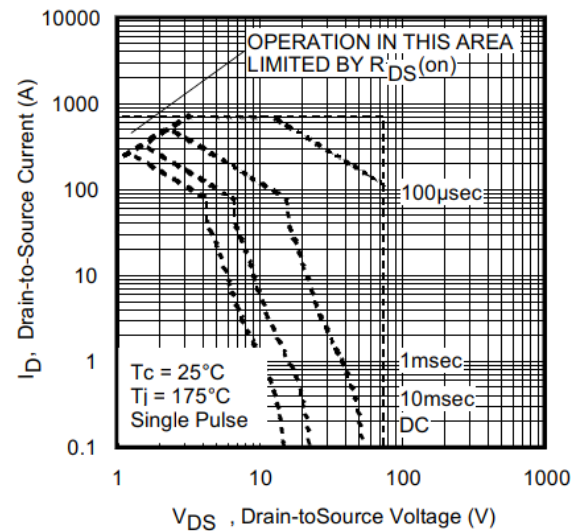


**Fig 8.** Maximum Safe Operating Area

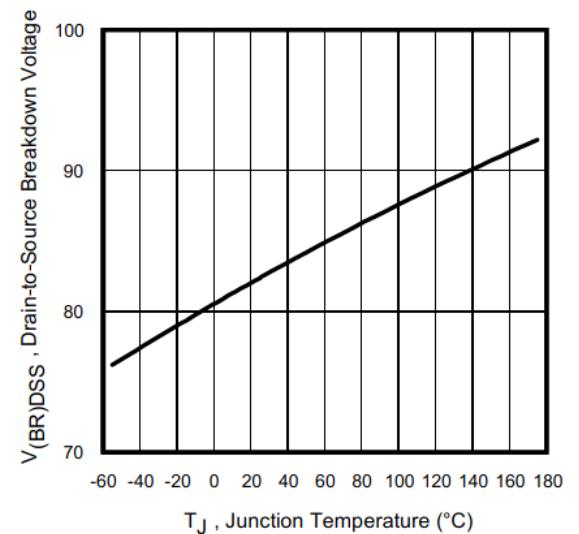


**Fig 10.** Drain-to-Source Breakdown Voltage

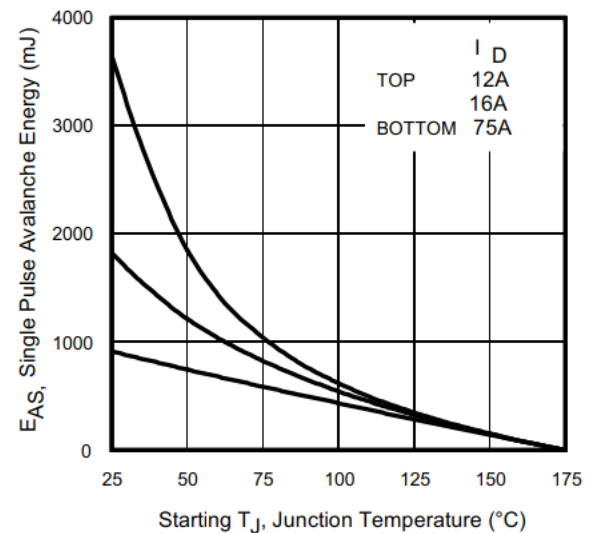


**Fig 12.** Maximum Avalanche Energy vs. Drain Current

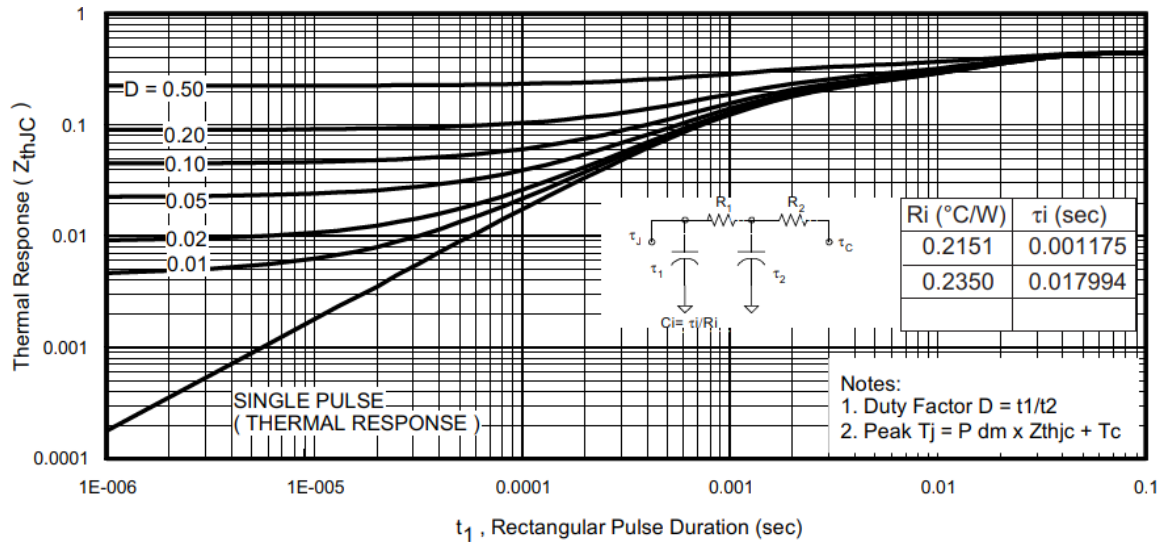


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

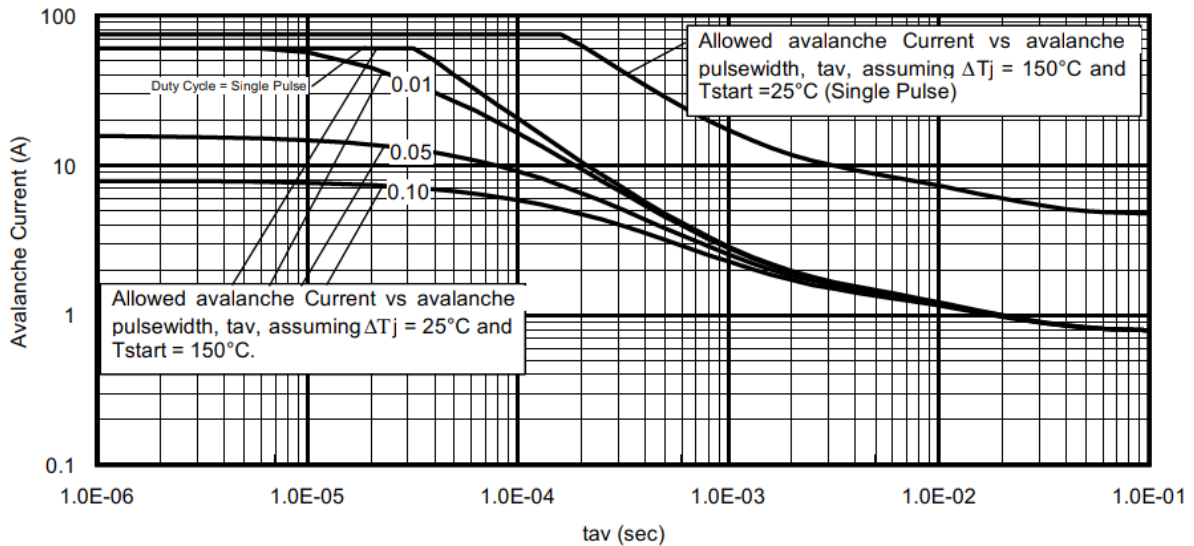


Fig 14. Avalanche Current vs. Pulse width

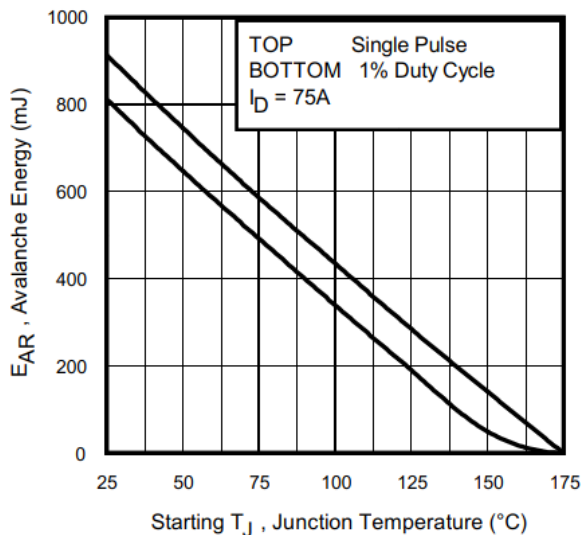


Fig 15. Maximum Avalanche Energy vs. Temperature

**Notes on Repetitive Avalanche Curves , Figures 14, 15:**  
 (For further info, see AN-1005 at [www.infineon.com](http://www.infineon.com))

1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 18a, 18b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5.  $BV$  = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as  $25^{\circ}\text{C}$  in Figure 13, 14).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see Figures 13)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{thJC}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

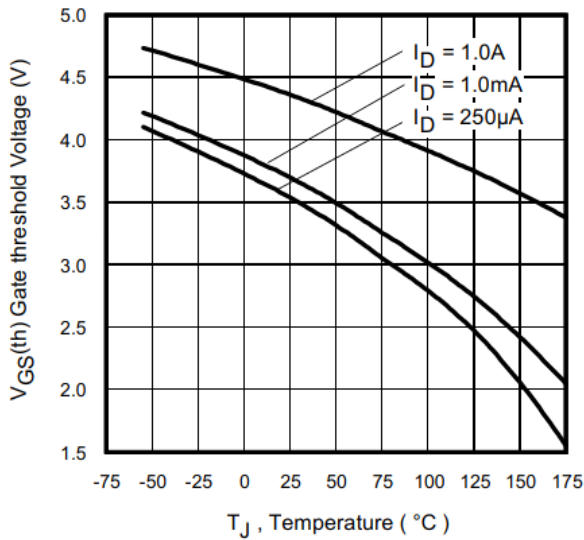


**Fig 16.** Threshold Voltage vs. Temperature

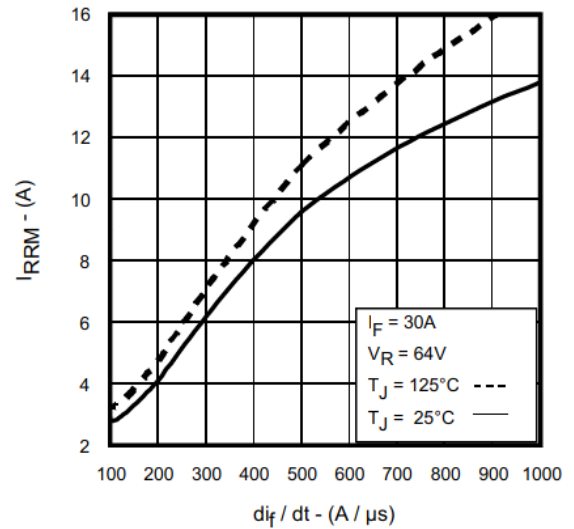


**Fig. 17 -** Typical Recovery Current vs.  $di/dt$

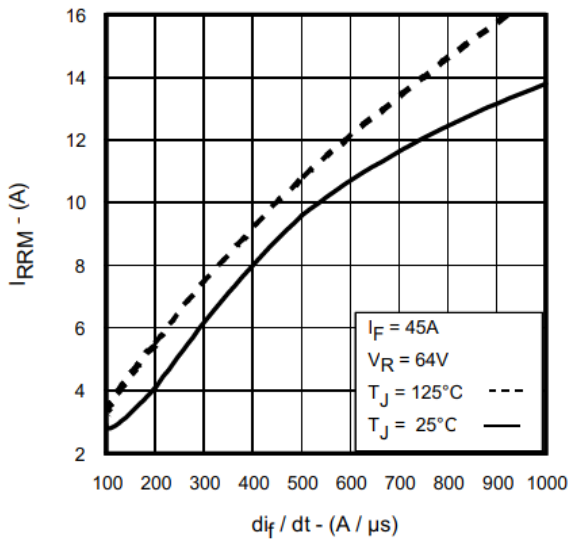


**Fig. 18 -** Typical Recovery Current vs.  $di/dt$

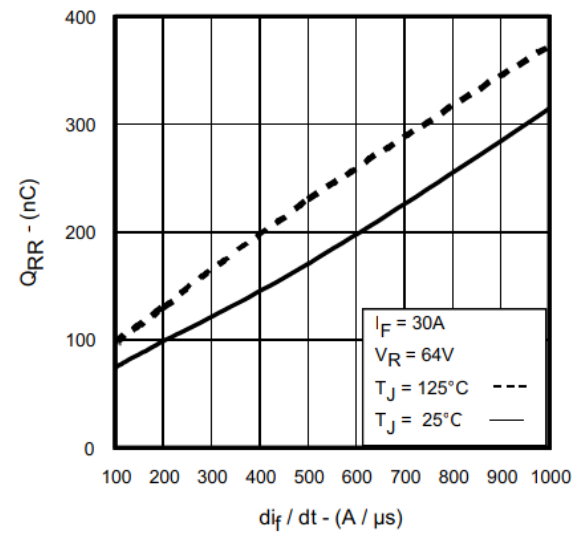


**Fig. 19 -** Typical Stored Charge vs.  $di/dt$

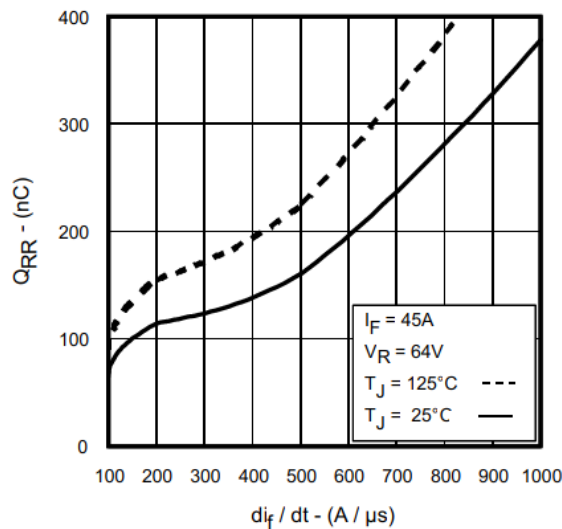


**Fig. 20 -** Typical Stored Charge vs.  $di/dt$

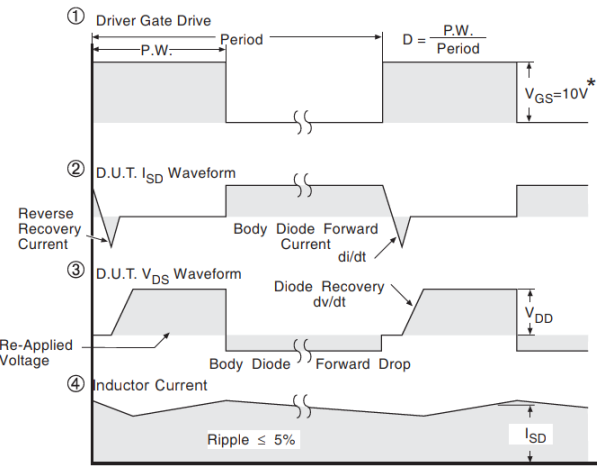
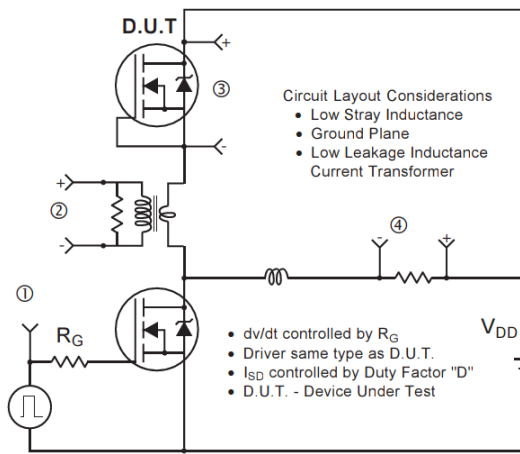


**Fig 21. Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET® Power MOSFETs**

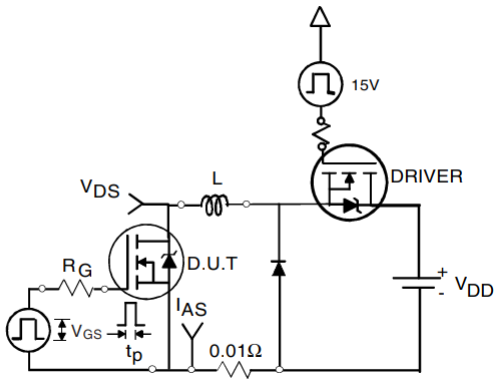


**Fig 22a. Unclamped Inductive Test Circuit**

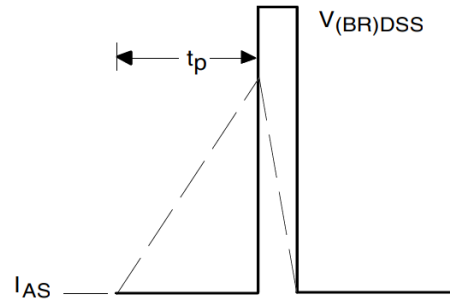


**Fig 22b. Unclamped Inductive Waveforms**

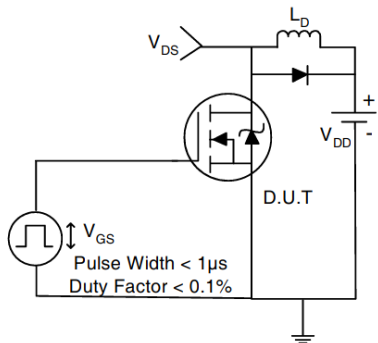


**Fig 23a. Switching Time Test Circuit**

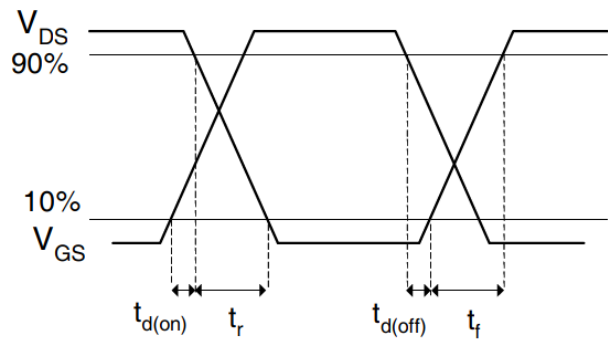


**Fig 23b. Switching Time Waveforms**

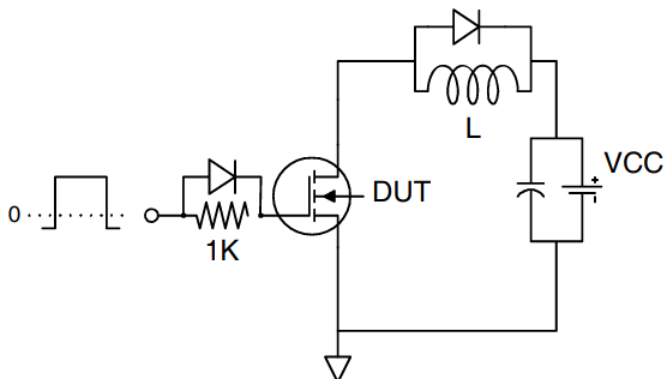


**Fig 24a. Gate Charge Test Circuit**

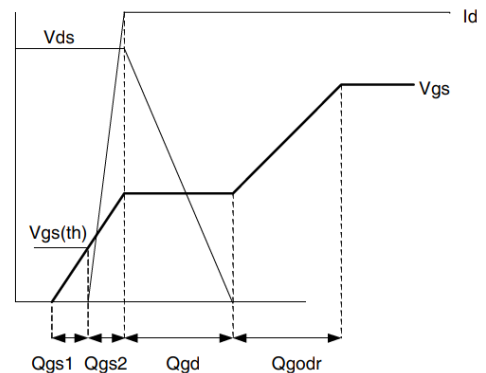
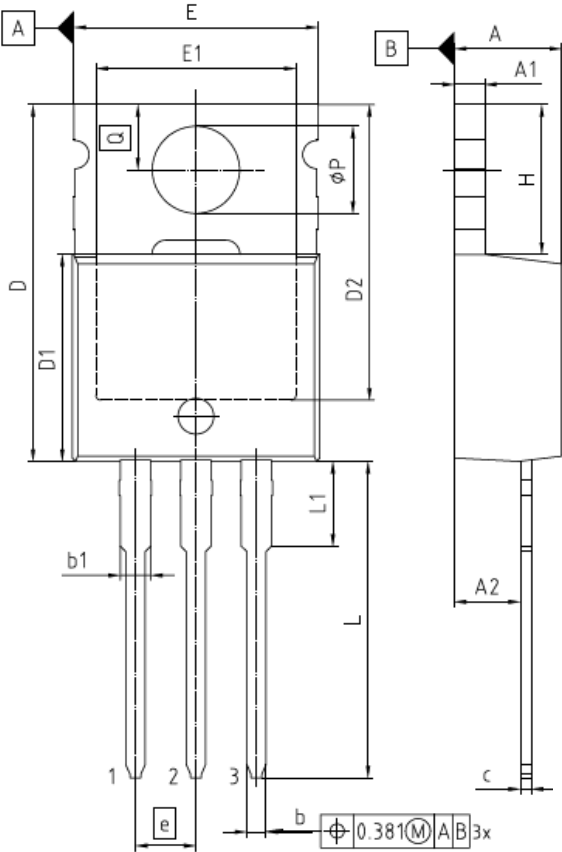


**Fig 24b. Gate Charge Waveform**

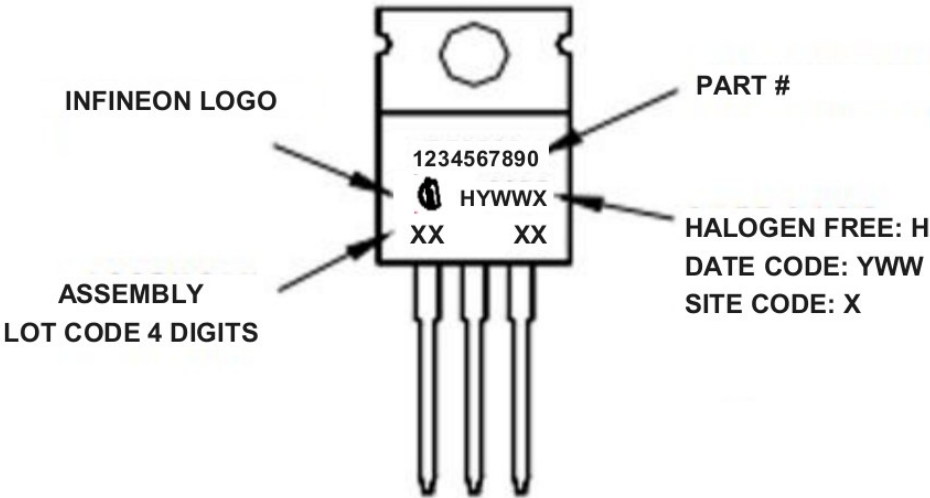
TO-220 Package Outline (Dimensions are shown in millimeters (inches))



NOTES:  
DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS  
GATE BURRS ARE LESS THAN 0.5 mm

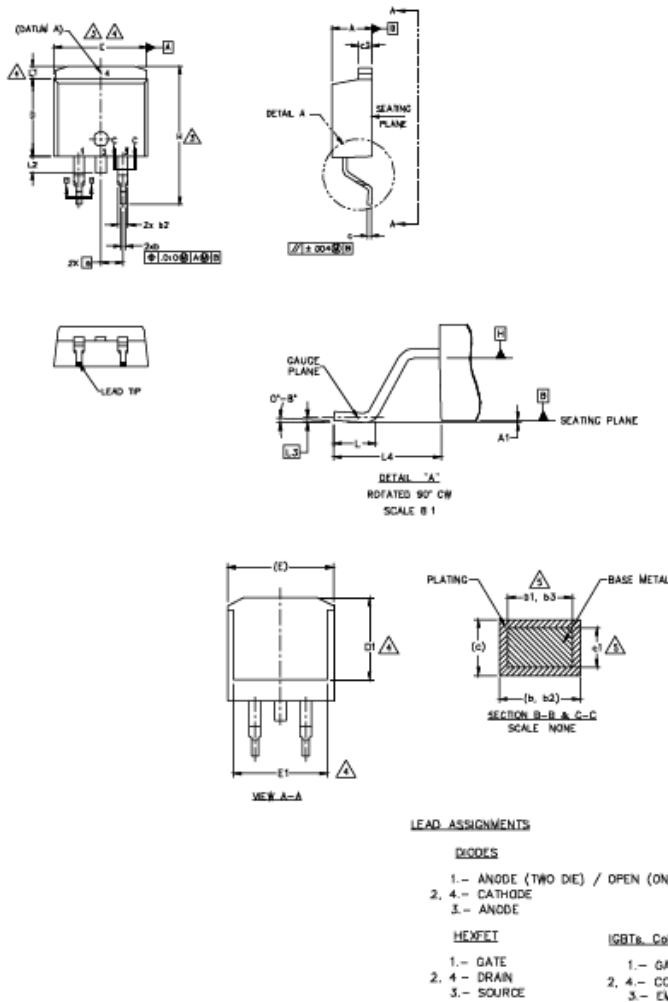
| PACKAGE - GROUP<br>NUMBER: PG-TO220-3-U05 |             |       |
|-------------------------------------------|-------------|-------|
| DIMENSIONS                                | MILLIMETERS |       |
|                                           | MIN.        | MAX.  |
| A                                         | 3.56        | 4.83  |
| A1                                        | 1.14        | 1.40  |
| A2                                        | 2.03        | 2.92  |
| b                                         | 0.38        | 1.01  |
| b1                                        | 1.14        | 1.78  |
| c                                         | 0.36        | 0.61  |
| D                                         | 14.22       | 16.51 |
| D1                                        | 8.38        | 9.20  |
| D2                                        | 11.68       | 12.88 |
| E                                         | 9.65        | 10.67 |
| E1                                        | 6.86        | 8.89  |
| e                                         | 2.54        |       |
| N                                         | 3           |       |
| H                                         | 5.84        | 6.86  |
| L                                         | 12.70       | 14.73 |
| L1                                        | 3.56        | 4.06  |
| ØP                                        | 3.54        | 4.08  |
| Q                                         | 2.54        | 3.42  |

TO-220 Part Marking Information



TO-220 packages are not recommended for Surface Mount Application.

D<sup>2</sup> Pak (TO-263AB) Package Outline (Dimensions are shown in millimeters (inches))



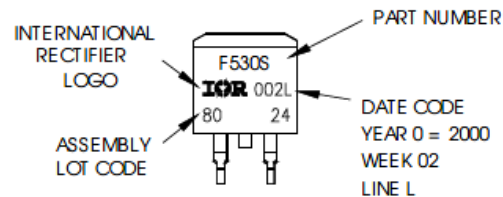
| SYMBOL | DIMENSIONS  |       |          |      | NOTES |
|--------|-------------|-------|----------|------|-------|
|        | MILLIMETERS |       | INCHES   |      |       |
|        | MIN.        | MAX.  | MIN.     | MAX. |       |
| A      | 4.06        | 4.83  | .160     | .190 | 5     |
| A1     | 0.00        | 0.254 | .000     | .010 |       |
| b      | 0.51        | 0.99  | .020     | .039 |       |
| b1     | 0.51        | 0.89  | .020     | .035 |       |
| b2     | 1.14        | 1.78  | .045     | .070 |       |
| b3     | 1.14        | 1.73  | .045     | .068 | 5     |
| c      | 0.38        | 0.74  | .015     | .029 | 5     |
| c1     | 0.38        | 0.58  | .015     | .023 |       |
| c2     | 1.14        | 1.65  | .045     | .065 |       |
| D      | 8.38        | 9.65  | .330     | .380 | 3     |
| D1     | 6.86        | —     | .270     |      | 4     |
| E      | 9.65        | 10.67 | .380     | .420 | 3,4   |
| E1     | 6.22        | —     | .245     |      | 4     |
| e      | 2.54 BSC    |       | .100 BSC |      | 4     |
| H      | 14.61       | 15.88 | .575     | .625 |       |
| L      | 1.78        | 2.79  | .070     | .110 |       |
| L1     | —           | 1.65  | —        | .066 |       |
| L2     | —           | 1.78  | —        | .070 |       |
| L3     | 0.25 BSC    |       | .010 BSC |      | 4     |
| L4     | 4.78        | 5.28  | .188     | .208 |       |

- NOTES
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
  3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
  4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1
  5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY
  6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
  7. CONTROLLING DIMENSION INCH.
  8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

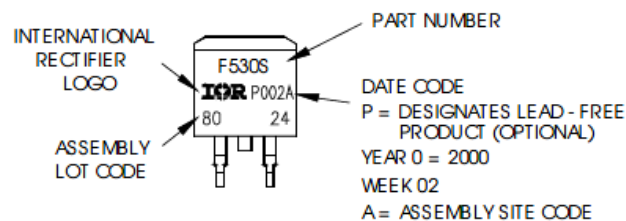
D<sup>2</sup> Pak (TO-263AB) Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH  
LOT CODE 8024  
ASSEMBLED ON WW/02, 2000  
IN THE ASSEMBLY LINE "L"

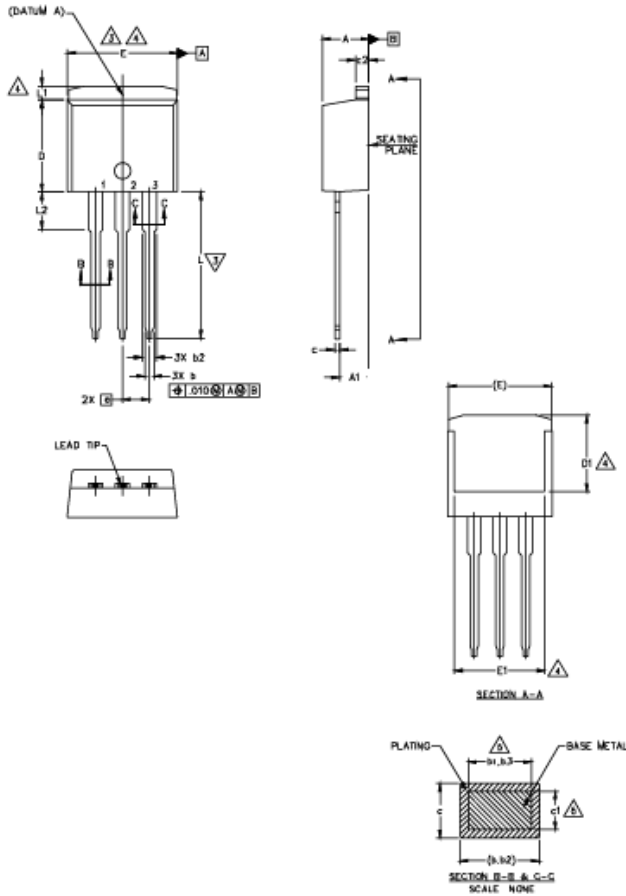
Note: "P" in assembly line position  
indicates "Lead - Free"



OR



TO-262 Package Outline (Dimensions are shown in millimeters (inches))



NOTES

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
6. CONTROLLING DIMENSION INCH.
7. OUTLINE CONFORM TO JEDEC TO-262 EXCEPT A1(max.), b(min.) AND D1(min.) WHERE DIMENSIONS DERIVED THE ACTUAL PACKAGE OUTLINE.

| SYMBOL | DIMENSIONS  |       |          |      | NOTES |
|--------|-------------|-------|----------|------|-------|
|        | MILLIMETERS |       | INCHES   |      |       |
|        | MIN.        | MAX.  | MIN.     | MAX. |       |
| A      | 4.06        | 4.83  | .160     | .190 | 5     |
| A1     | 2.03        | 3.02  | .080     | .119 |       |
| b      | 0.51        | 0.99  | .020     | .039 |       |
| b1     | 0.51        | 0.89  | .020     | .035 |       |
| b2     | 1.14        | 1.78  | .045     | .070 | 5     |
| b3     | 1.14        | 1.73  | .045     | .068 |       |
| c      | 0.38        | 0.74  | .015     | .029 |       |
| c1     | 0.38        | 0.58  | .015     | .023 | 5     |
| c2     | 1.14        | 1.65  | .045     | .065 | 3     |
| D      | 8.38        | 9.65  | .330     | .380 |       |
| D1     | 6.86        | —     | .270     | —    |       |
| E      | 9.65        | 10.67 | .380     | .420 |       |
| E1     | 6.22        | —     | .245     | —    | 4     |
| e      | 2.54 BSC    |       | .100 BSC |      | 4     |
| L      | 13.48       | 14.10 | .530     | .555 |       |
| L1     | —           | 1.65  | —        | .065 |       |
| L2     | 3.56        | 3.71  | .140     | .146 |       |

LEAD ASSIGNMENTS

HEXFET

- 1.— GATE
- 2.— DRAIN
- 3.— SOURCE
- 4.— DRAIN

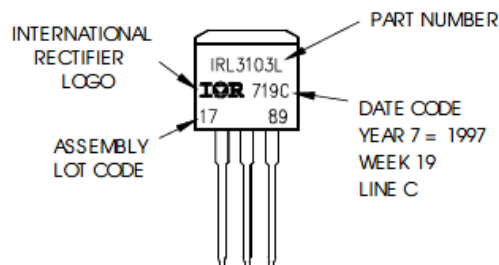
IGBTs, CoPACK

- 1.— GATE
- 2.— COLLECTOR
- 3.— EMITTER
- 4.— COLLECTOR

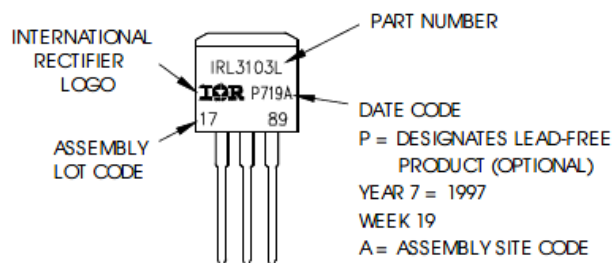
TO-262 Part Marking Information

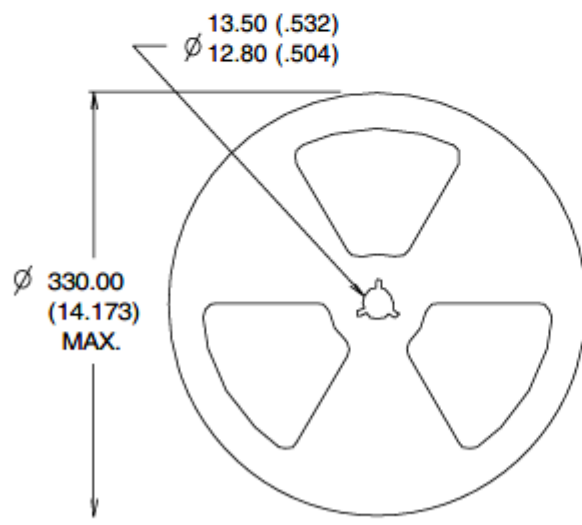
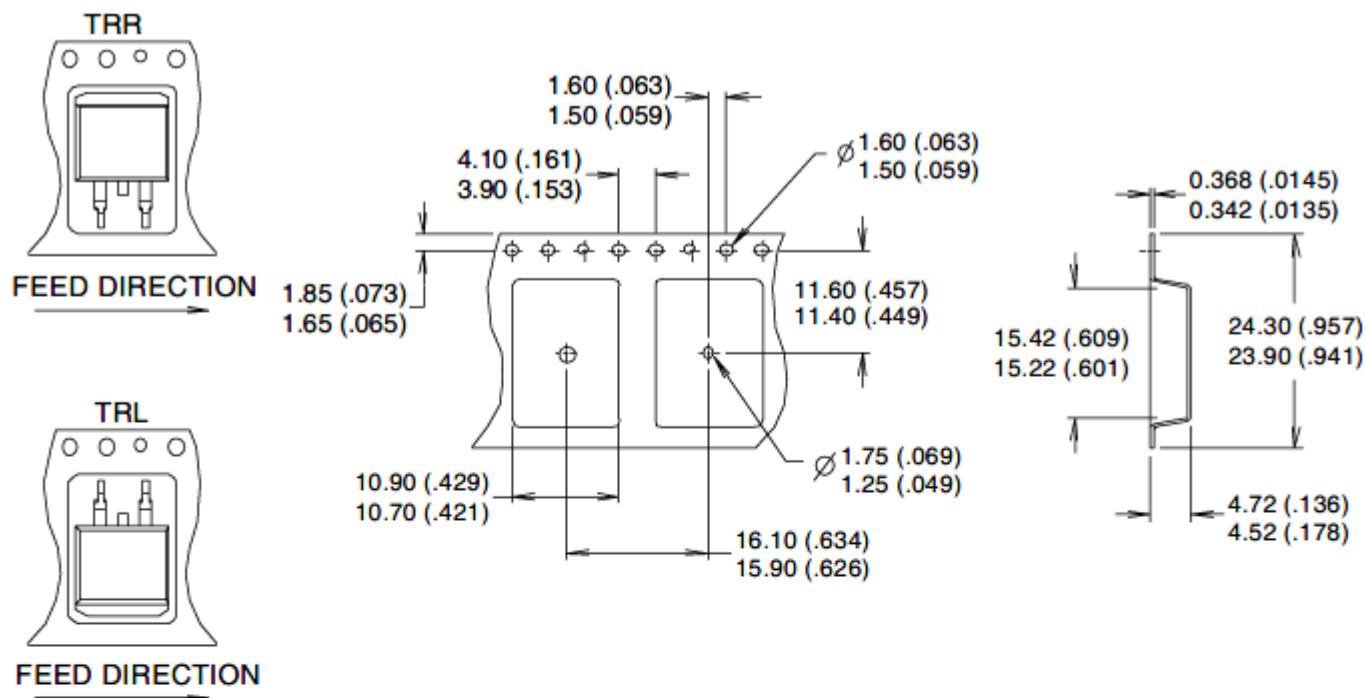
EXAMPLE: THIS IS AN IRL3103L  
LOT CODE 1789  
ASSEMBLED ON WW 19, 1997  
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead - Free"

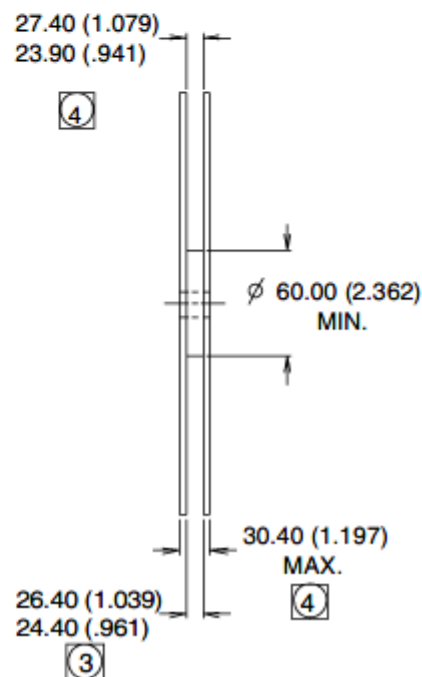


OR



**D<sup>2</sup> Pak (TO-263AB) Tape & Reel Information** (Dimensions are shown in millimeters (inches))

**NOTES :**

1. COMFORMS TO EIA-418.
2. CONTROLLING DIMENSION: MILLIMETER.
- ③ DIMENSION MEASURED @ HUB.
- ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.



## Revision History

| Date       | Rev. | Comments                                                                                                                                                                                |
|------------|------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| 2026-07-29 | 2.1  | <ul style="list-style-type: none"> <li>Update datasheet to Infineon format</li> <li>Updated Package Outline and Part marking –page 8</li> <li>Added disclaimer on last page.</li> </ul> |

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